L Number	Hits	Search Text	DB	Time stamp
1	21	(semiconductor near laser) and (active near (layer or region or medium or film)) and (protection near (film or layer or region or medium)) and ridge and (refractive near (index or indice)) and (open$5) and (shap$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/18 11:31
-	34	(semiconductor near laser) and (active near (layer or region or medium or film)) and (protection near (film or layer or region or medium)) and ridge and (refractive near (index or indice))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/17 09:25
-	28	((semiconductor near laser) and (active near (layer or region or medium or film)) and (protection near (film or layer or region or medium)) and ridge and (refractive near (index or indice))) and width	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/20 13:54
-	12	(semiconductor near laser) and ((active near (layer or region or medium or film)) SAME (protection near (film or layer or region or medium)) SAME (SUBSTRATE)) and ridge and (refractive near (index or indice))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/20 10:37
-	21	(semiconductor near laser) and ((active near (layer or region or medium or film)) AND (protection near (film or layer or region or medium)) SAME (SUBSTRATE)) and ridge and (refractive near (index or indice))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/20 15:02
-	17	((semiconductor near laser) and ((active near (layer or region or medium or film)) AND (protection near (film or layer or region or medium)) SAME (SUBSTRATE)) and ridge and (refractive near (index or indice))) and width	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/20 14:24
-	10	((semiconductor near laser) and ((active near (layer or region or medium or film)) SAME (protection near (film or layer or region or medium)) SAME (SUBSTRATE)) and ridge and (refractive near (index or indice))) and width	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/20 14:24
-	12	(semiconductor near laser) and ((active near (layer or region or medium or film)) AND (protection near (film or layer or region or medium)) SAME (SUBSTRATE)) and (width same ridge) and (refractive near (index or indice))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/20 16:36
-	11	((semiconductor near laser) and ((active near (layer or region or medium or film)) AND (protection near (film or layer or region or medium)) SAME (SUBSTRATE)) and (width same ridge) and (refractive near (index or indice))) and 372/$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/21 08:26
-	456	(semiconductor near laser) and (active near (layer or region or medium or film)) and ((dielectric or insulat$5 or protect$5) near (film or layer or region or medium)) and ridge and (refractive near (index or indice))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/21 10:56
-	382	(semiconductor near laser) and (active near (layer or region or medium or film)) and ((dielectric or insulat$5 or protect$5) near (film or layer or region or medium)) and ridge and (refractive near (index or indice)) AND substrate and width	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/21 10:59
-	0	(semiconductor near laser) and (active near (layer or region or medium or film)) and (((dielectric or insulat$5 or protect$5) near (film or layer or region or medium)) same substrat) and ridge and (refractive near (index or indice)) and width	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/22 13:14

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-	284	(semiconductor near laser) and (active near (layer or region or medium or film)) and (((dielectric or insulat$5 or protect$5) near (film or layer or region or medium)) same substrate) and ridge and (refractive near (index or indice)) and width	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/22 13:18
-	131	(semiconductor near laser) and (active near (layer or region or medium or film)) and (((dielectric or insulat$5 or protect$5) near (film or layer or region or medium)) same substrate same ridge) and (refractive near (index or indice)) and width	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/22 13:21
-	29	(semiconductor near laser) and (active near (layer or region or medium or film)) and (((dielectric or insulat$5 or protect$5) near (film or layer or region or medium)) same substrate same ridge same (refractive near (index or indice))) and width	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/22 14:31
-	23	((semiconductor near laser) and (active near (layer or region or medium or film)) and (((dielectric or insulat$5 or protect$5) near (film or layer or region or medium)) same substrate same ridge same (refractive near (index or indice))) and width) and 372/$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/22 14:31
-	6	((semiconductor near laser) and (active near (layer or region or medium or film)) and (((dielectric or insulat$5 or protect$5) near (film or layer or region or medium)) same substrate same ridge same (refractive near (index or indice))) and width) and 257/$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/22 14:32
-	12	(semiconductor near device) and (active near (layer or region or medium or film)) and (((dielectric or insulat$5 or protect$5) near (film or layer or region or medium)) same substrate same ridge same (refractive near (index or indice))) and width	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/22 14:36
-	30	(semiconductor near (device or laser)) and (active near (layer or region or medium or film)) and (((dielectric or insulat$5 or protect$5) near (film or layer or region or medium)) same substrate same ridge same (refractive near (index or indice))) and width	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/22 14:41
-	344	(semiconductor with optical) and substrate and (active near (layer or film or region or medium)) and ((protect$5 or insulat$5) near (film or layer or region or medium)) and ridge and refractive	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/31 10:54
-	114	(semiconductor with optical) and substrate and (active near (layer or film or region or medium)) and ((protect$5 or insulat$5) near (film or layer or region or medium)) and (ridge or groove) and refractive and (stripe near shaped)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/31 13:23
-	0	((semiconductor with optical) and substrate and (active near (layer or film or region or medium)) and ((protect$5 or insulat$5) near (film or layer or region or medium)) and (ridge or groove) and refractive and (stripe near shaped)) and (open$5 near center) and (open$5 near rear)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/31 13:33
-	108	((semiconductor with optical) and substrate and (active near (layer or film or region or medium)) and ((protect$5 or insulat$5) near (film or layer or region or medium)) and (ridge or groove) and refractive and (stripe near shaped)) and width	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/31 13:38
-	90	(((semiconductor with optical) and substrate and (active near (layer or film or region or medium)) and ((protect$5 or insulat$5) near (film or layer or region or medium)) and (ridge or groove) and refractive and (stripe near shaped)) and width) and 372/$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/31 13:38

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| - | 27 | (semiconductor near laser) and (active near (layer or region or medium or film)) and (protection near (film or layer or region or medium)) and ridge and (refractive near (index or indice)) and (open$5) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/06/18 11:28 |

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